

# 8192 BIT STATIC MOS READ ONLY MEMORY

PROM ROM

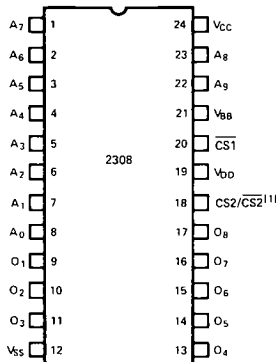
- **Fast Access Time: 450 ns**
- **Standard Power Supplies: +12V, ±5V**
- **TTL Compatible: All Inputs and Outputs**
- **Programmable Chip Select Input for Easy Memory Expansion**
- **Three-State Output: OR-Tie Capability**
- **Fully Decoded: On Chip Address Decode**
- **Inputs Protected: All Inputs Have Protection Against Static Charge**
- **Pin Compatible to 2708 PROM**

The Intel 2308 is a 8192 bit static MOS read only memory organized as 1024 words by 8-bits. This ROM is designed for memory applications where high performance, large bit storage, and simple interfacing are important design objectives.

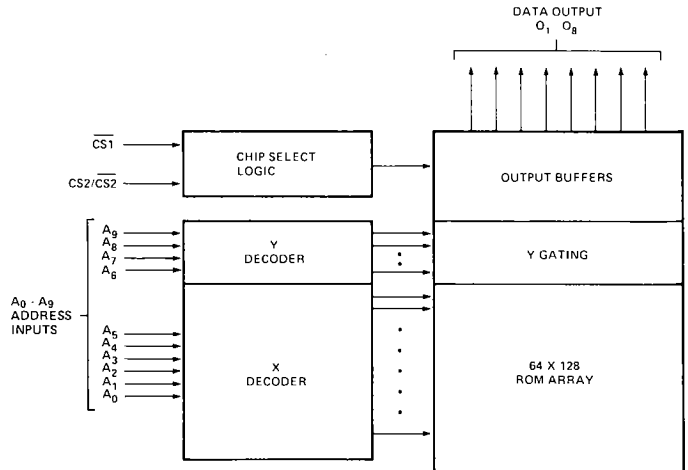
The inputs and outputs are TTL compatible. The chip select input ( $CS2/\overline{CS2}$ ) is programmable. An active high or low level chip select input can be defined by the designer and the desired chip select logic level is fixed at Intel during the masking process. The programmable chip select input, as well as OR-tie compatibility on the outputs, facilitates easy memory expansion. The pin compatible UV erasable 2708 PROM is available for initial system prototyping.

The 2308 read only memory is fabricated with N-channel silicon gate technology. This technology provides the designer with high performance, easy-to-use MOS circuits.

### PIN CONFIGURATION



### BLOCK DIAGRAM



### PIN NAMES

A <sub>0</sub> -A <sub>9</sub>	ADDRESS INPUTS
O <sub>1</sub> -O <sub>8</sub>	DATA OUTPUTS
CS <sub>1</sub>	CHIP SELECT INPUT
CS <sub>2</sub> /CS <sub>2(1)</sub>	PROGRAMMABLE CHIP SELECT INPUT

NOTE 1. The CS<sub>2</sub>/CS<sub>2</sub> LOGIC LEVELS MUST BE SPECIFIED BY THE USER AS EITHER A LOGIC 1 (V<sub>HH</sub>) OR LOGIC 0 (V<sub>LL</sub>). A LOGIC 0 SHOULD BE SPECIFIED IN ORDER TO BE COMPATIBLE WITH THE 2708.

### Absolute Maximum Ratings\*

Ambient Temperature Under Bias . . . . .	-25°C to +85°C
Storage Temperature . . . . .	-65°C to +150°C
Voltage On Any Pin With Respect To $V_{BB}$ . . . . .	-0.3V to 20V
Power Dissipation . . . . .	1.0 Watt

\*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

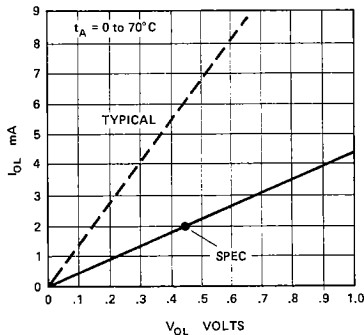
### D.C. and Operating Characteristics

$T_A = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ ,  $V_{CC} = 5\text{V} \pm 5\%$ ;  $V_{DD} = 12\text{V} \pm 5\%$ ,  $V_{BB} = -5\text{V} \pm 5\%$ ,  $V_{SS} = 0\text{V}$  Unless Otherwise Specified.

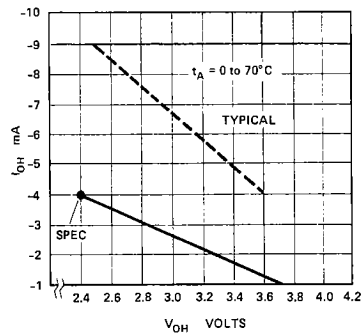
Symbol	Parameter	Limits			Unit	Test Conditions
		Min.	Typ.[1]	Max.		
$I_{LI}$	Input Load Current (All Input Pins Except $\overline{CS}_1$ )		1	10	$\mu\text{A}$	$V_{IN} = 0$ to $5.25\text{V}$
$I_{LCL}$	Input Load Current on $\overline{CS}_1$			1.6	$\text{mA}$	$V_{IN} = 0.45\text{V}$
$I_{LPC}$	Input Peak Load Current on $\overline{CS}_1$			4	$\text{mA}$	$0.8\text{V} \leq V_{IN} < 3.3\text{V}$
$I_{LKC}$	Input Leakage Current on $\overline{CS}_1$			10	$\mu\text{A}$	$V_{IN} = 3.3\text{V}$ to $5.25\text{V}$
$I_{LO}$	Output Leakage Current			10	$\mu\text{A}$	Chip Deselected
$V_{IL}$	Input "Low" Voltage	$V_{SS}-1$		0.8V	V	
$V_{IH}$	Input "High" Voltage	3.3		$V_{CC}+1.0$	V	
$V_{OL}$	Output "Low" Voltage			0.45	V	$I_{OL} = 2\text{mA}$
$V_{OH1}$	Output "High" Voltage	2.4			V	$I_{OH} = -4\text{mA}$
$V_{OH2}$	Output "High" Voltage	3.7			V	$I_{OH} = -1\text{mA}$
$I_{CC}$	Power Supply Current $V_{CC}$		10	15	$\text{mA}$	
$I_{DD}$	Power Supply Current $V_{DD}$		32	60	$\text{mA}$	
$I_{BB}$	Power Supply Current $V_{BB}$		$10\mu\text{A}$	1	$\text{mA}$	
$P_D$	Power Dissipation		460	840	$\text{mW}$	

NOTE 1: Typical values for  $T_A = 25^\circ\text{C}$  and nominal supply voltage

D.C. OUTPUT CHARACTERISTICS



D.C. OUTPUT CHARACTERISTICS



**A.C. Characteristics**

T<sub>A</sub> = 0°C to +70°C, V<sub>CC</sub> = +5V ±5%; V<sub>DD</sub> = +12V ±5%, V<sub>BB</sub> = -5V ±5%, V<sub>SS</sub> = 0V, Unless Otherwise Specified.

Symbol	Parameter	Limits <sup>[2]</sup>		Unit
		Typ.	Max.	
t <sub>ACC</sub>	Address to Output Delay Time	200	450	ns
t <sub>CO1</sub>	Chip Select 1 to Output Delay Time	85	160	ns
t <sub>CO2</sub>	Chip Select 2 to Output Delay Time	125	220	ns
t <sub>DF</sub>	Chip Deselect to Output Data Float Time	125	220	ns

**NOTE 2:** Refer to conditions of Test for A.C. Characteristics. Add 50 nanoseconds (worst case) to specified values at V<sub>OH</sub> = 3.7V @ I<sub>OH</sub> = -1mA, C<sub>L</sub> = 100pF.

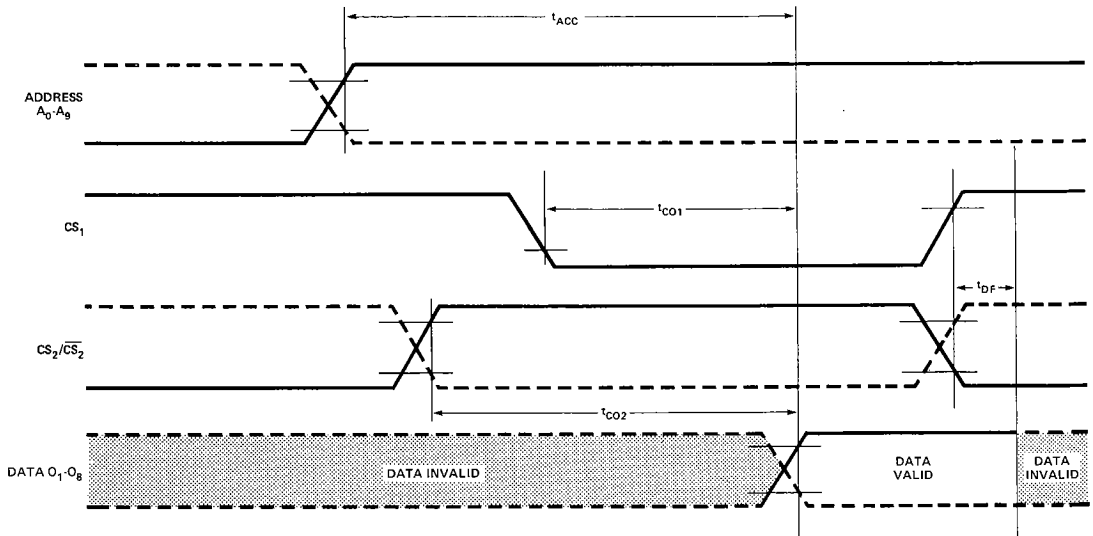
**CONDITIONS OF TEST FOR A.C. CHARACTERISTICS**

Output Load . . . . . 1 TTL Gate, and C<sub>LOAD</sub> = 100pF  
 Input Pulse Levels . . . . . .65V to 3.3V  
 Input Pulse Rise and Fall Times . . . . . 20 nsec  
 Timing Measurement Reference Level  
 . . . . . 2.4V V<sub>IH</sub>, V<sub>OH</sub>; 0.8V V<sub>IL</sub>, V<sub>OL</sub>

**CAPACITANCE\*** T<sub>A</sub> = 25°C, f = 1 MHz, V<sub>BB</sub> = -5V, V<sub>DD</sub>, V<sub>CC</sub> and all other pins tied to V<sub>SS</sub>.

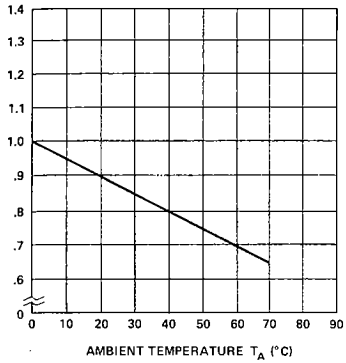
Symbol	Test	Limits	
		Typ.	Max.
C <sub>IN</sub>	Input Capacitance		6pF
C <sub>OUT</sub>	Output Capacitance		12pF

\*This parameter is periodically sampled and is not 100% tested.

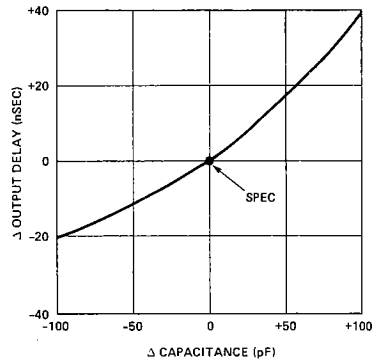


**Typical Characteristics** (Nominal supply voltages unless otherwise noted.)

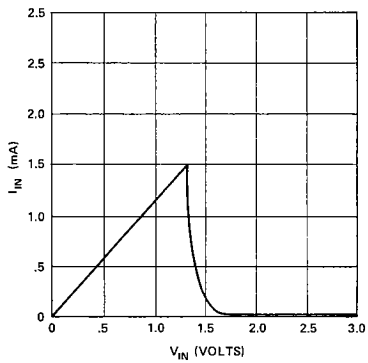
**I<sub>DD</sub> VS. TEMPERATURE  
(NORMALIZED)**



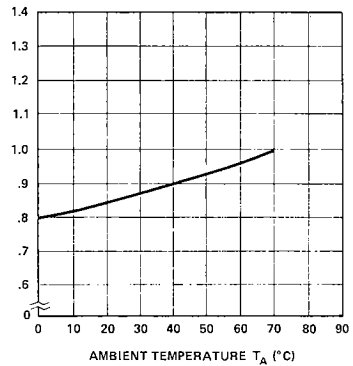
**Δ OUTPUT CAPACITANCE  
VS. Δ OUTPUT DELAY**



**$\overline{CS}_1$  INPUT  
CHARACTERISTICS**



**T<sub>ACC</sub> VS. TEMPERATURE  
(NORMALIZED)**



PROM/ROM